

## FEATURES

High density cell design for low  $R_{DS(ON)}$   
Voltage controlled small signal switch  
Rugged and reliable  
High saturation current capability

$V_{DSS}$  60 V  
 $I_D$  340 mA  
 $R_{DS(ON)}$  1.7  $\Omega$

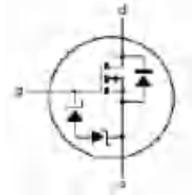
7002

### SOT-23

1. GATE
2. SOURCE
3. DRAIN



### Equivalent Circuit



## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum ratings (  $T_a=25^\circ\text{C}$  unless otherwise noted)

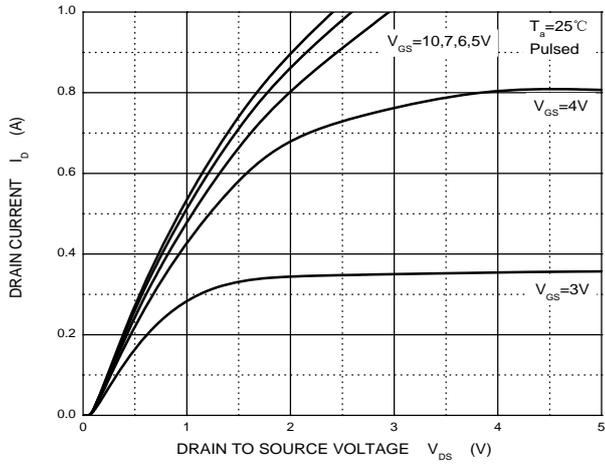
Symbol	Parameter	Value	Units
$V_{DS}$	Drain-Source voltage	60	V
$V_{GS}$	Gate-Source voltage	20	V
$I_D$	Drain Current	340	mA
$P_D$	Power Dissipation	0.35	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	357	$^\circ\text{C/W}$

## Electrical Characteristics

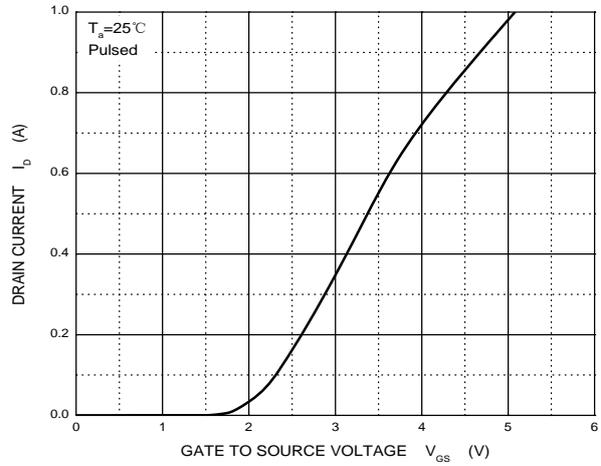
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Gate Threshold Voltage*	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1mA$	1		2.5	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 48V, V_{GS} = 0V$			1	$\mu A$
Gate -Source leakage current	$I_{GSS1}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 10$	$\mu A$
	$I_{GSS2}$	$V_{GS} = \pm 10V, V_{DS} = 0V$			$\pm 200$	nA
	$I_{GSS3}$	$V_{GS} = \pm 5V, V_{DS} = 0V$			$\pm 100$	nA
Drain-Source On-Resistance*	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 200mA$		1.7	5.3	$\Omega$
		$V_{GS} = 10V, I_D = 500mA$			5	$\Omega$
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 300mA$			1.5	V
Recovered charge	$Q_r$	$V_{GS} = 0V, I_S = 300mA, V_R = 25V, di/dt = -100A/\mu S$		30		nC
<b>Dynamic Characteristics**</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$			40	pF
Output Capacitance	$C_{oss}$				30	pF
Reverse Transfer Capacitance	$C_{rss}$				10	pF
<b>Switching Characteristics**</b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DD} = 50V, R_G = 50\Omega, R_{GS} = 50\Omega, R_L = 250\Omega$			10	ns
Turn-Off Delay Time	$t_{d(off)}$				15	ns
Reverse recovery Time	$t_{rr}$	$V_{GS} = 0V, I_S = 300mA, V_R = 25V, di/dt = -100A/\mu S$		30		ns
<b>GATE-SOURCE ZENER DIODE</b>						
Gate-Source Breakdown Voltage	$BV_{GSO}$	$I_{GS} = \pm 1mA$ (Open Drain)	$\pm 21.5$		$\pm 30$	V

RATING AND CHARACTERISTIC CURVES

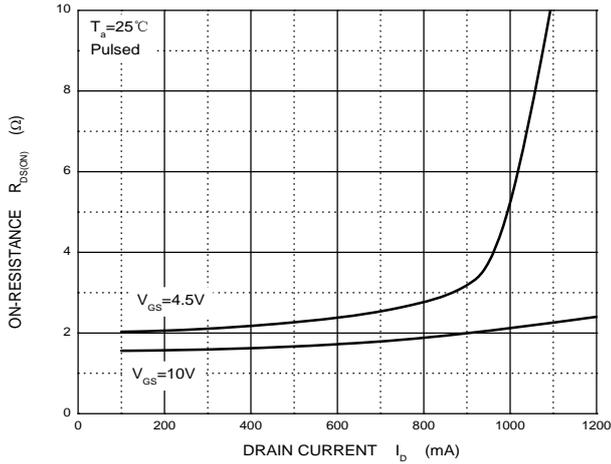
Output Characteristics



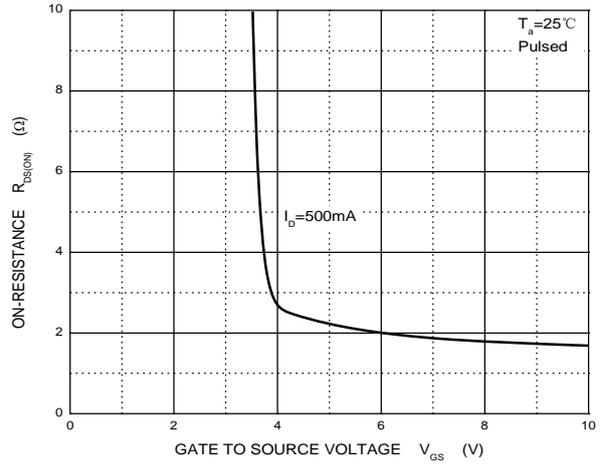
Transfer Characteristics



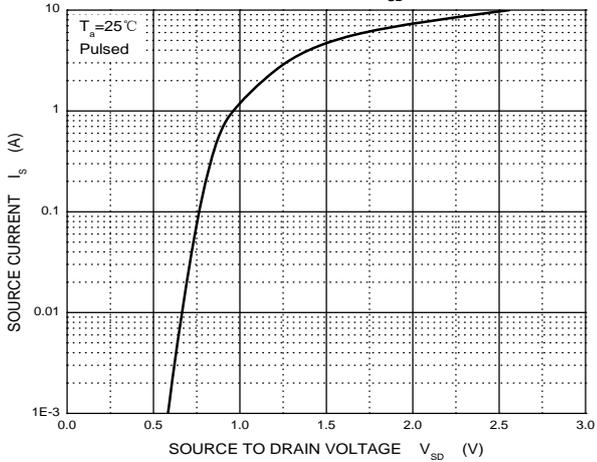
$R_{DS(ON)}$  —  $I_D$



$R_{DS(ON)}$  —  $V_{GS}$

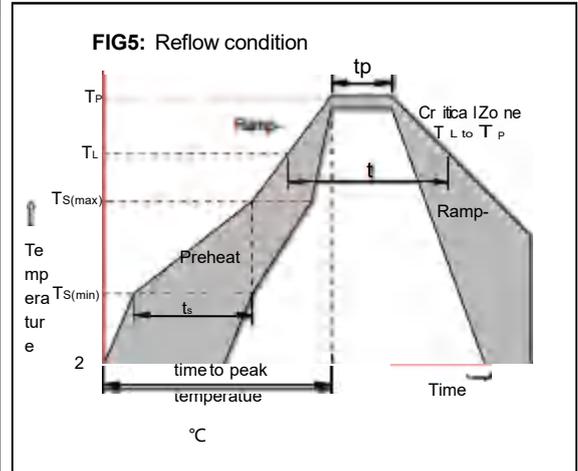


$I_S$  —  $V_{SD}$



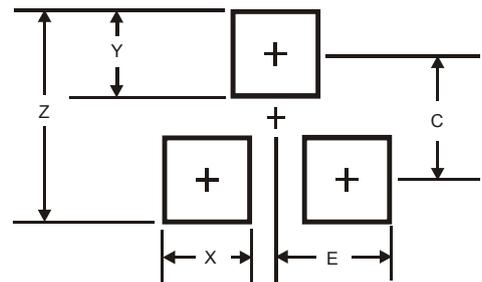
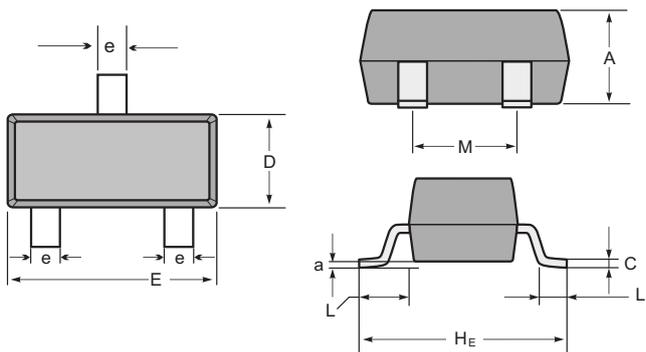
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ( $T_{s(min)}$ )	+150 °C
	-Temperature Max( $T_{s(max)}$ )	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp ( $T_L$ ) to peak)		3 °C/sec. Max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature( $T_L$ )(Liquid us)	+217 °C
	-Temperature( $t_L$ )	60-150 secs.
Peak Temp ( $T_P$ )		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp ( $t_p$ )		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp ( $T_P$ )		8 min. Max
Do not exceed		+260 °C



Package Dimensions & Suggested Pad Layout

SOT23



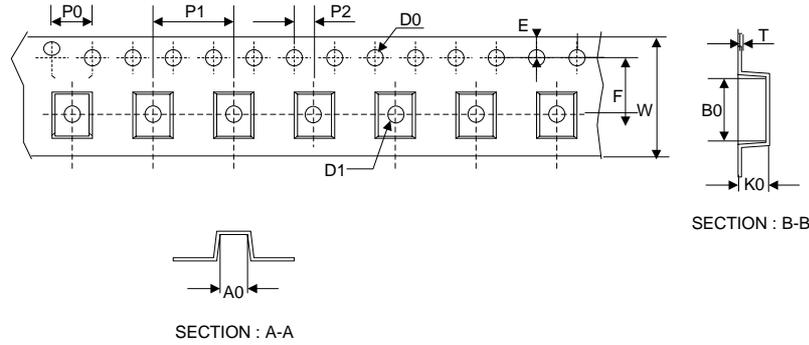
SOT-23 mechanical data

UNIT	A	C	D	E	HE	e	M	L	L1	a	
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Dimensions	SOT23
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

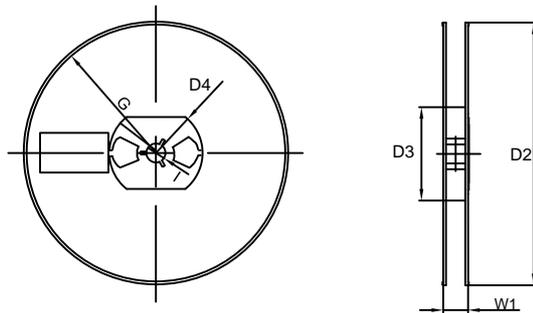
Tape & reel specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.10
P1	4.00±0.10
P2	2.00±0.10
D0	1.55±0.10
D1	1.05±0.10
E	1.55±0.10
F	3.60±0.10
W	8.00±0.10
A0	3.80±0.20
B0	3.25±0.20
K0	1.45±0.10
T	0.25±0.05
D2	178.0±3.0
D3	55Min.
D4	R24.0±3.0
G	R82.0±3.0
I	13.0±2.0
W1	11.0±3.0

7" Reel



Quantity: 3000PCS